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# P-Channel 40 V (D-S) MOSFET

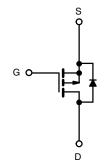
PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}$ (m $\Omega$ )(Typ.)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)			
- 40	12.5 at V <sub>GS</sub> = - 10 V	- 60	40 0			
- 40	16 at V <sub>GS</sub> = - 4.5 V	- 60	40 nC			

#### **FEATURES**

- DT-Trench Power MOSFET
- 100 % Rg and UIS Tested
- · Excellent package for good heat dissipation

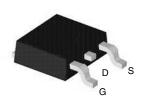
#### **APPLICATIONS**

- Power switching application
- · Hard switched and high frequency circuits
- Uninterruptible power supply



P-Channel MOSFET

#### TO-252 Pin Configuration



Top View

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V <sub>DS</sub>	- 40	V		
Gate-Source Voltage	V <sub>GS</sub>	± 20			
Continuous Drain Current (T <sub>.1</sub> = 150 °C) <sup>a</sup>	T <sub>C</sub> = 25 °C	l <sub>D</sub>	- 60		
Continuous Drain Current (1) = 150°C)	T <sub>C</sub> = 100 °C		- 39.5	Α	
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	- 180			
Single Pulse Avalanche Energy		E <sub>AS</sub>	110	mJ	
Maximum Power Dissipation <sup>c</sup>	T <sub>C</sub> = 25 °C	В	73.5	W	
Maximum Fower Dissipation	T <sub>C</sub> = 100 °C	P <sub>D</sub>	29.4		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB mount d	R <sub>thJA</sub>	50	°C/W		
Junction-to-Case		$R_{thJC}$	1.7	C/VV		

#### Notos

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 40			٧	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zoro Gato Voltago Drain Current	l	V <sub>DS</sub> = - 40 V, V <sub>GS</sub> = 0 V			- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 32 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			- 10	μA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V	- 60			Α	
Durin Course On Otata Basistana a	B	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 20 A		12.5	15		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 10 A		16	21	mΩ	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 5 V, I <sub>D</sub> = -20 A		45		S	
Dynamic <sup>b</sup>				•	•		
Input Capacitance	C <sub>iss</sub>			2560		pF	
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		207			
Reverse Transfer Capacitance	C <sub>rss</sub>			197			
Total Gate Charge	Qg			40			
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -20 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -20 \text{ A}$		7		nC	
Gate-Drain Charge	Q <sub>gd</sub>			8.5			
Gate Resistance	$R_g$	f = 1 MHz		3.2		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			12			
Rise Time	t <sub>r</sub>	$V_{DD} = -20 \text{ V}, I_{D} = -20 \text{ A},$		20		ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	VGEN = - 10 V, Rg = 3 $\Omega$		40			
Fall Time	t <sub>f</sub>			27			
<b>Drain-Source Body Diode Characteristics</b>				•			
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 60	Α	
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				- 180		
Body Diode Voltage	$V_{SD}$	I <sub>S</sub> = - 1 A			- 1.2	V	
Body Diode Reverse Recovery Time	ody Diode Reverse Recovery Time t <sub>rr</sub>			38		ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	$I_F = -20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		45		nC	

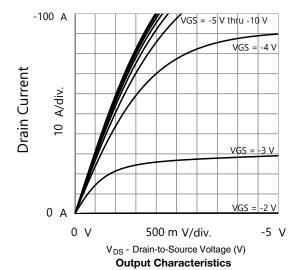
#### Notes:

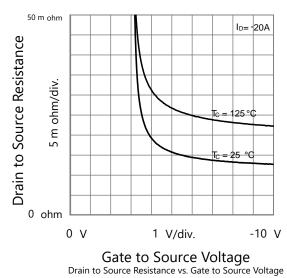
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

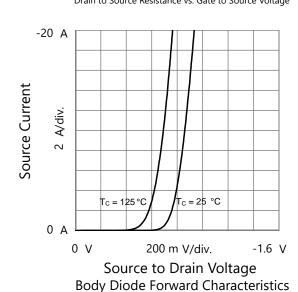
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

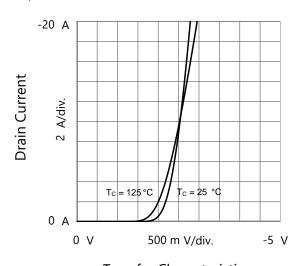
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

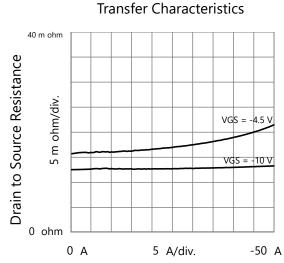




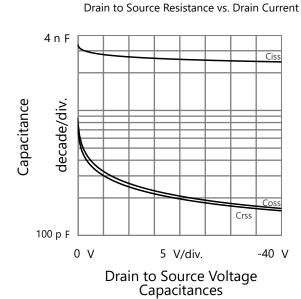






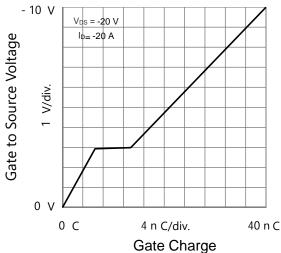


**Drain Current** 

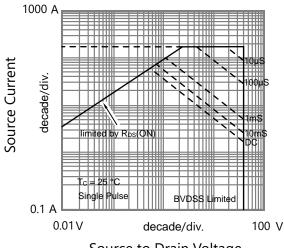




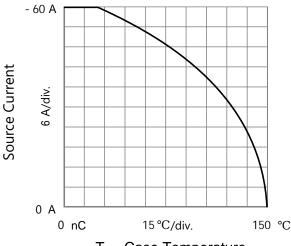
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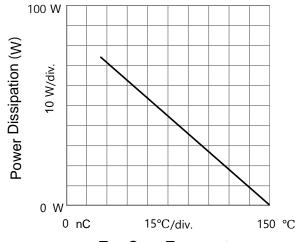
Gate Charge
Gate to Source Voltage vs. GateCharge



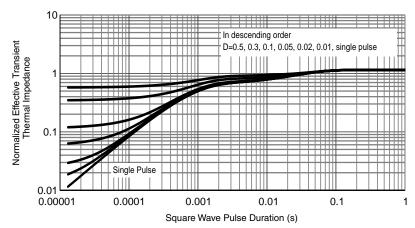
Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



T<sub>C</sub> - Case Temperature Current Derating

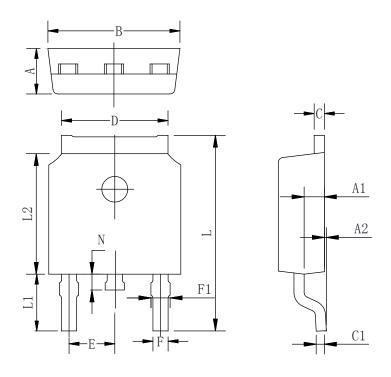


 $T_C \textbf{- Case Temperature}_{\text{Current Derating}}$ 



Normalized Thermal Transient Impedance, Junction-to-Case

# TO-252-2L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max	
A	2.10	2.30	2.50	
A1	0.88	1.01	1.16	
A2	0.00	0.15	0.28	
В	6.40	6.60	6.80	
С	0.42	0.50	0.63	
C1	0.42	0.50	0.63	
D	5.08	5.32	5.65	
Е	2.286 TYP			
F	0.63	0.76	0.89	
F1	0.64	0.86	1.08	
L	9.30	9.90	10.80	
L1	2.4	2.8	3.6	
L2	5.90	6.10	6.55	
N	0.57	0.80	1.05	

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